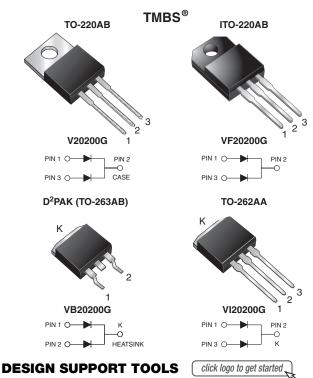
V20200G-E3, VF20200G-E3, VB20200G-E3, VI20200G-E3

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Dual High Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.62 \text{ V}$ at $I_F = 5 \text{ A}$





PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 10 A				
V_{RRM}	200 V				
I _{FSM}	110 A				
V_F at $I_F = 10 A$	0.71 V				
T_J max.	150 °C				
Package	TO-220AB, ITO-220AB, D ² PAK (TO-263AB), TO-262AA				
Circuit configuration	Common cathode				

FEATURES

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses
- High efficiency operation
- · Low thermal resistance

RoHS

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB and TO-262AA package)
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, D 2 PAK (TO-263AB), and TO-262AA

Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS compliant, commercial grade

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: as marked

Mounting Torque: 10 in-lbs max.

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	V20200G	VF20200G	VB20200G	VI20200G	UNIT	
Max. repetitive peak reverse voltage	V_{RRM}	200			•	V	
May graves forward restified gravent (fig. 1)		20			Α		
Max. average forward rectified current (fig. 1) per diode	I _{F(AV)}	10					
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	110		Α			
Non-repetitive avalanche energy at T _J = 25 °C, L = 60 mH per diode	E _{AS}	E _{AS} 60			mJ		
Peak repetitive reverse current at t_p = 2 μ s, 1 kHz, T_J = 38 °C \pm 2 °C per diode		0.5		Α			
Voltage rate of change (rated V _R)		10 000			V/µs		
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min	V _{AC}	1500			V		
Operating junction and storage temperature range	T _J , T _{STG}		-40 t	o +150		°C	

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V20200G-E3, VF20200G-E3, VB20200G-E3, VI20200G-E3

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	$I_R = 1.0 \text{ mA}$	T _J = 25 °C	V_{BR}	200 (min.)	ı	V	
Instantaneous forward voltage per diode (1)	$I_F = 5 A$	T _J = 25 °C	V _F	0.86	-	V	
	I _F = 10 A			1.23	1.70		
	I _F = 5 A	T _J = 125 °C		0.62	-		
	$I_F = 10 \text{ A}$			0.71	0.80		
Reverse current per diode (2)	V _R = 180 V	T _J = 25 °C	I _R	1.9	ı	μA	
		T _J = 125 °C		1.6	ı	mA	
	V _R = 200 V	T _J = 25 °C		-	150	μA	
		T _J = 125 °C		2.5	15	mA	

Notes

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	V20200G	VF20200G	VB20200G	VI20200G	UNIT	
Typical thermal resistance per diode	$R_{\theta JC}$	3.2	5.5	3.2	3.2	°C/W	

ORDERING INFORMATION (EXAMPLE)								
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
TO-220AB	V20200G-E3/4W	1.88	4W	50/tube	Tube			
ITO-220AB	VF20200G-E3/4W	1.75	4W	50/tube	Tube			
TO-263AB	VB20200G-E3/4W	1.39	4W	50/tube	Tube			
TO-263AB	VB20200G-E3/8W	1.39	8W	800/reel	Tape and reel			
TO-262AA	VI20200G-E3/4W	1.45	4W	50/tube	Tube			

RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

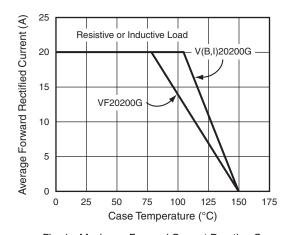


Fig. 1 - Maximum Forward Current Derating Curve

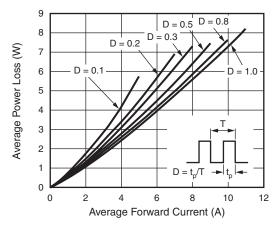


Fig. 2 - Forward Power Loss Characteristics Per Diode

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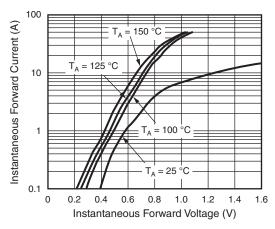


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

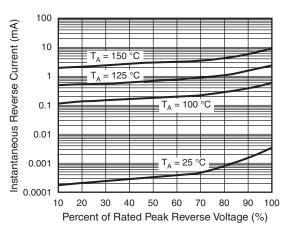


Fig. 4 - Typical Reverse Characteristics Per Diode

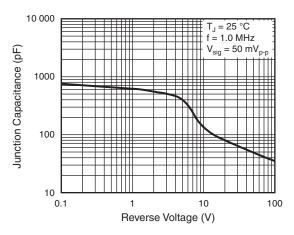


Fig. 5 - Typical Junction Capacitance Per Diode

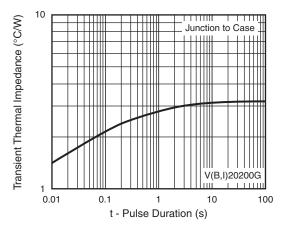


Fig. 6 - Typical Transient Thermal Impedance Per Diode

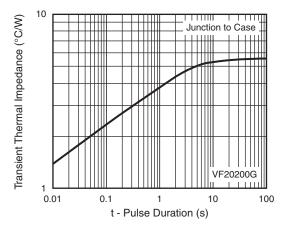


Fig. 7 - Typical Transient Thermal Impedance Per Diode

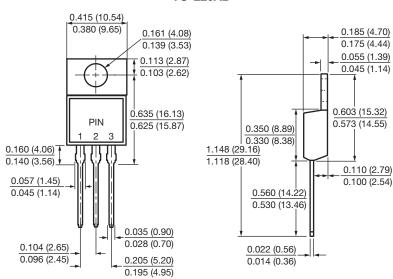


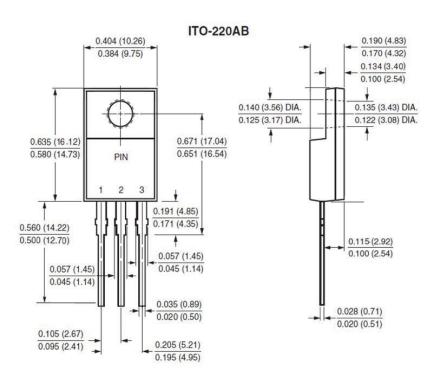
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

TO-220AB



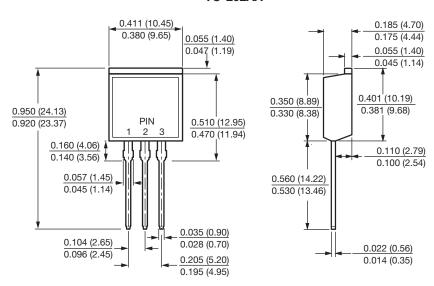




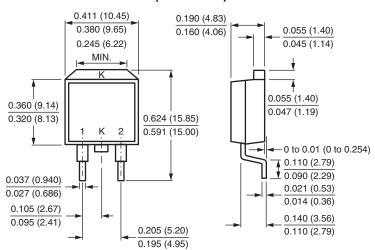
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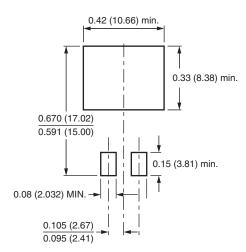
TO-262AA



D²PAK (TO-263AB)



Mounting Pad Layout





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